

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION N	0. F	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/718,959		11/21/2003	Geun Su Lee	30205/39514	4436
4743	7590	05/04/2005		EXAMINER	
	•	STEIN & BORUN	LEE, SIN J		
233 S. WA		IVE, SUITE 6300		ART UNIT	PAPER NUMBER
CHICAG	O, IL 6060	6		1752	

DATE MAILED: 05/04/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)
Office Action Summan	10/718,959	LEE, GEUN SU
Office Action Summary	Examiner	Art Unit
The MAILING DATE of this communication and	Sin J. Lee	1752
The MAILING DATE of this communication app Period for Reply	bears on the cover sheet with the d	correspondence address
A SHORTENED STATUTORY PERIOD FOR REPL' THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl - If NO period for reply is specified above, the maximum statutory period of the	36(a). In no event, however, may a reply be tin y within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from t, cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. (D) (35 U.S.C. § 133).
Status	·	
 1) Responsive to communication(s) filed on 18 Ja 2a) This action is FINAL. 2b) This 3) Since this application is in condition for alloward closed in accordance with the practice under E 	s action is non-final. nce except for formal matters, pro	
Disposition of Claims		•
 4) ☐ Claim(s) 1-20 is/are pending in the application 4a) Of the above claim(s) is/are withdray 5) ☐ Claim(s) 4-7 is/are allowed. 6) ☐ Claim(s) 1-3,8 and 11-20 is/are rejected. 7) ☐ Claim(s) 9 and 10 is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or 	wn from consideration.	
Application Papers		
9)☐ The specification is objected to by the Examine 10)☒ The drawing(s) filed on 21 November 2003 is/a Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11)☐ The oath or declaration is objected to by the Example 11.	are: a)⊠ accepted or b)⊡ object drawing(s) be held in abeyance. Se tion is required if the drawing(s) is ob	e 37 CFR 1.85(a). ejected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119		
a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority document application from the International Burea	es have been received. Es have been received in Applicat rity documents have been receive u (PCT Rule 17.2(a)).	ion No ed in this National Stage
Attachment(s)		
1) Notice of References Cited (PTO-892)	4) 🔲 Interview Summary	/ (PTO-413)
2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	Paper No(s)/Mail D	

Art Unit: 1752

DETAILED ACTION

1. In view of the amendment of January 18, 2005, previous rejection on claim 3 under 35 U.S.C. 112, second paragraph is hereby withdrawn.

Claim Rejections - 35 USC § 102

- 2. The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.
- 3. Claims 1, 3, 8, and 11-20 are rejected under 35 U.S.C. 102(b) as being anticipated by Nishimura et al (EP 1 164 434 A2).

In Example 17 (see Table 1 of pg.54 and [0288]), Nishimura teaches a radiation sensitive resin composition containing 90 parts by weight of Resin A-23, 2.5 parts by weight of a photoacid generator, and 530 parts by weight of a solvent (propylene glycol monomethyl ether acetate). The Resin A-23 is described in [0277], and it has the following structure;

$$\begin{array}{ccccc} & & & & & & & & & \\ & & & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & \\ & & & \\ &$$

wherein the copolymerization molar ratio of the repeat unit (I-1) and (III-1) is 50.50. On pg.11, lines 30-53, Nishimura teaches the equivalence of the –CH₃ in the α -position of the repeat unit (III-1) and a hydrogen atom (see line 53 where it is stated that R⁶

represents a hydrogen atom or methyl group). Since there are only two choices for R^6 , one of ordinary skill in the art would immediately envisage the repeat unit (III-1) shown above in which the $-CH_3$ group in the α -position is replaced with a H atom, and the moiety of $-C(CH_3)(C(=O)-O-methyladamantyl)$ - in (III-1), in which $-CH_3$ group in the α -position is replaced with a H atom, teaches present unit "b". Present unit "c" can be 0 mol%. Also, present claim language of claims 1 and 3 *does not exclude* the presence of other moieties such as $-CH_2$ - moiety as in (III-1). Therefore, the prior art teaches present photoresist polymer of claims 1 and 3. Therefore, Nishimura teaches present inventions of claims 1, 3, 8, and 12.

With respect to present claim 11, since Nishimura uses 90 parts by weight of Resin A-23 and 2.5 parts by weight of a photoacid generator, this gives 2.8 wt.% of the photoacid generator based on the amount of the resin. Therefore, the prior art teaches present invention of claim 11.

With respect to present claim 13, since Nishimura uses 90 parts by weight of Resin A-23 and 530 parts by weight of the solvent, this gives 589 wt.% based on the amount of the resin. Therefore, the prior art teaches present invention of claim 13.

Nishimura teaches (see [0200]-[0204] and [0215]) that a resist pattern is formed from his radiation-sensitive resin composition by applying the composition solution to a substrate such as a silicon wafer to form a resist film, pre-baking the coated resist film, exposing it to radiation such as visible rays, UV rays, deep UV rays, X-rays, electron beams or the like (particularly preferable radiation being *ArF excimer laser* or *KrF excimer laser*), performing post-exposure bake at 90°C, and then developing the

Application/Control Number: 10/718,959

Art Unit: 1752

exposed resist film using an alkaline aqueous solution to form a predetermined resist pattern. Therefore, Nishimura teaches present inventions of claims 14-19 (since Nishimura teaches the same kinds of radiation source as the present invention, it is the Examiner's position that the prior art would inherently teach the present exposure energy range of claim 18).

With respect to present claim 20, Nishimura teaches ([0289]) that his radiation-sensitive resin composition is capable of producing semiconductors at a high yield without producing resolution defects during microfabrication. Therefore, the prior art teaches present invention of claim 20.

Claim Rejections - 35 USC § 103

- 4. The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.
- 5. Claim 2 is rejected under 35 U.S.C. 103(a) as being unpatentable over Nishimura et al (EP 1 164 434 A2).

In the Resin A-23 shown above, the repeat unit (III-1) has the 2-methyl-2-adamantyl group as the acid-labile group, and on pg.11, lines 30-50, lines 53-58, and [0066]-[0068], Nishimura teaches the equivalence of the 2-methyl-2-adamantyl group and t-butyl group (i.e., all R⁷ groups of the formula (4) on pg.11 are methyl groups). Because the prior art teaches the equivalence of these two groups, it would have been obvious to one of ordinary skill in the art to replace the 2-methyl-2-adamantyl group in the repeat unit (III-1) of Resin A-23 with a t-butyl group (as an acid-labile group) with a reasonable expectation of obtaining a resin composition exhibiting high transmittance of

Application/Control Number: 10/718,959 Page 5

Art Unit: 1752

radiation, high sensitivity, resolution, and pattern shape. Therefore, Nishimura's teaching would render obvious present invention of claim 2.

Allowable Subject Matter

- 6. Claims 9 and 10 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims. Nishimura does not teach or suggest the use of present photoacid generator of claim 9 in combination with his inventive resin.
- 7. Claims 4-7 are allowed. Nishimura does not teach or suggest present method of forming the photoresist polymer of Formula 1.

Response to Arguments

8. Applicants argue that Nishimura does not teach or suggest present polymer of the formula 1 because the repeat unit (III-1) of Nishimura's polymer (as shown above) includes a methacrylate group unit in the main chain (i.e., it includes the moiety of -CH₂-in addition to the single carbon moiety having an ester group) whereas present polymer includes a repeat unit including a single carbon moiety having an ester group (when c is not present) or two single carbon ester moieties (when c is present). Although the Examiner understands what applicants are trying to explain, the polymer of Nishimura still meets present Formula 1 of claim 1 and Formula 3 of claim 3 because present claim language of those claims does not exclude the presence of —CH₂- moiety as in (III-1) of Nishimura's polymer: claim 1 uses the transitional phrase "comprising" in its preamble.

Art Unit: 1752

9. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

10. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Sin J. Lee whose telephone number is 571-272-1333. The examiner can normally be reached on Monday-Friday from 9:00 am EST to 5:30 pm EST.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Cynthia Kelly, can be reached on 571-272-1526. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should

Application/Control Number: 10/718,959

Art Unit: 1752

Page 7

you have questions on access to the Private PAIR system, contact the Electronic

Business Center (EBC) at 866-217-9197 (toll-free).

J. A. J.

S. Lee

April 29, 2005

Sin f. Lee Sin J. Lee

Patent Examiner

Technology Center 1700

TECHNOLOGY WILLS